NXP USA Inc. - FS32K142HFT0MLHT Datasheet





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Applications of "<u>Embedded -</u> <u>Microcontrollers</u>"

Details

Product Status	Active
Core Processor	ARM® Cortex®-M4F
Core Size	32-Bit Single-Core
Speed	80MHz
Connectivity	CANbus, FlexIO, I ² C, LINbus, SPI, UART/USART
Peripherals	POR, PWM, WDT
Number of I/O	58
Program Memory Size	256KB (256K x 8)
Program Memory Type	FLASH
EEPROM Size	4K x 8
RAM Size	32K x 8
Voltage - Supply (Vcc/Vdd)	2.7V ~ 5.5V
Data Converters	A/D 16x12b SAR; D/A1x8b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 125°C (TA)
Mounting Type	Surface Mount
Package / Case	64-LQFP
Supplier Device Package	64-LQFP (10x10)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/fs32k142hft0mlht

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1 Block diagram

Following figures show superset high level architecture block diagrams of S32K14x series and S32K11x series respectively. Other devices within the family have a subset of the features. See Feature comparison for chip specific values.



Figure 1. High-level architecture diagram for the S32K14x family

3.2 Ordering information



Product status

P: Prototype F: Qualified

Product type/brand S32: Automotive 32-bit MCU

Product line K: Arm Cortex MCUs

Series/Family

1: 1st product series 2: 2nd product series

Core platform/Performance

- 1: Arm Cortex M0+
- 4: Arm Cortex M4F

Memory size

	2	4	6	8
S32K11x			128K	256K
S32K14x	256K	512K	1M	2M

Ordering option

X: Speed

B: 48 MHz without DMA (S32K11x only) L: 48 MHz with DMA (S32K11x only) H: 80 MHz U¹: 112 MHz (Not valid with M temperature/125C)

Y: Optional feature

- R: Base feature set
- F: CAN FD, FlexIO
- A1: CAN FD, FlexIO, Security
- E: Ethernet, Serial Audio Interface (S32K148 only) J¹: Ethernet, Serial Audio Interface, CAN FD, FlexIO, Security (S32K148 only)

Wafer, Fab and revision

Fx: ATMC² Tx: GF XX: Flex #²

x0: 1st revision

Temperature

V: -40C to 105C M: -40C to 125C W: -40C to 150C²

Package

Pins	LQFP	QFN	BGA
32	-	FM	-
48	LF	-	-
64	LH	-	-
100	LL	-	мн
144	LQ	-	-
176	LU	-	-

Tape and Reel T: Trays/Tubes R: Tape and Reel

1. CSEc (Security) or EEPROM writes/erase will trigger error flags in HSRUN mode (112 MHz) because this use case is not allowed to execute simultaneously. The device will need to switch to RUN mode (80 MHz) to execute CSEc (Security) or EEPROM writes/erase.

2. Not supported yet

3. Part numbers no longer offered as standard include:

Ordering Option X (M:64MHz); Ordering Option Y (N: limited RAM. 16KB for K142, 48KB for K144, 96KB for K146, 192KB for K148 S: Security); Temperature (C: -40C to 85C)

NOTE

Not all part number combinations are available. See S32K1xx_Orderable_Part_Number_List.xlsx attached with the Datasheet for list of standard orderable parts.

Figure 4. Ordering information

4.4 Power and ground pins



NOTE: V_{DD} and V_{DDA} must be shorted to a common source on PCB

Figure 5. Pinout decoupling

Table 4. Supplies decoupling capacitors 1, 2

Symbol	Description	Min. ³	Тур.	Max.	Unit
C _{REF} ^{, 4} , ⁵	ADC reference high decoupling capacitance	70	100	—	nF
C _{DEC} ⁵ , ⁶ , ⁷	Recommended decoupling capacitance	70	100		nF

V_{DD} and V_{DDA} must be shorted to a common source on PCB. The differential voltage between V_{DD} and V_{DDA} is for RF-AC only. Appropriate decoupling capacitors to be used to filter noise on the supplies. See application note AN5032 for reference supply design for SAR ADC. All V_{SS} pins should be connected to common ground at the PCB level.

2. All decoupling capacitors must be low ESR ceramic capacitors (for example X7R type).

3. Minimum recommendation is after considering component aging and tolerance.

4. For improved performance, it is recommended to use 10 µF, 0.1 µF and 1 nF capacitors in parallel.

5. All decoupling capacitors should be placed as close as possible to the corresponding supply and ground pins.

6. Contact your local Field Applications Engineer for details on best analog routing practices.

7. The filtering used for decoupling the device supplies must comply with the following best practices rules:

• The protection/decoupling capacitors must be on the path of the trace connected to that component.

• No trace exceeding 1 mm from the protection to the trace or to the ground.

• The protection/decoupling capacitors must be as close as possible to the input pin of the device (maximum 2 mm).

• The ground of the protection is connected as short as possible to the ground plane under the integrated circuit.

I/O parameters

- 6. Several I/O have both high drive and normal drive capability selected by the associated Portx_PCRn[DSE] control bit. All other GPIOs are normal drive only. For details see IO Signal Description Input Multiplexing sheet(s) attached with the *Reference Manual*.
- 7. When using ENET and SAI on S32K148, the overall device limits associated with high drive pin configurations must be respected i.e. On 144-pin LQFP the general purpose pins: PTA10, PTD0, and PTE4 must be set to low drive.
- 8. Measured at input $V = V_{SS}$
- 9. Measured at input $V = V_{DD}$

5.4 DC electrical specifications at 5.0 V Range

Symbol	Parameter		Value		Unit	Notes
		Min.	Тур.	Max.		
V _{DD}	I/O Supply Voltage	4	_	5.5	V	
V _{ih}	Input Buffer High Voltage	0.65 x V _{DD}	_	V _{DD} + 0.3	V	1
V _{il}	Input Buffer Low Voltage	V _{SS} – 0.3	_	0.35 x V _{DD}	V	2
V _{hys}	Input Buffer Hysteresis	0.06 x V _{DD}	—	_	V	
Ioh _{GPIO}	I/O current source capability measured	5	—	—	mA	
loh _{GPIO-HD_DSE_0}	when pad V _{oh} = (V _{DD} - 0.8 V)					
Iol _{GPIO}	I/O current sink capability measured	5	—	_	mA	
Iol _{GPIO-HD_DSE_0}	when pad V _{ol} = 0.8 V					
Ioh _{GPIO-HD_DSE_1}	I/O current source capability measured when pad $V_{oh} = V_{DD} - 0.8 V$	20	_	_	mA	3
Iol _{GPIO-HD_DSE_1}	I/O current sink capability measured when pad $V_{ol} = 0.8 V$	20	_	-	mA	3
loh _{GPIO-FAST_DSE_0}	I/O current sink capability measured when pad $V_{oh} = V_{DD} - 0.8 V$	14.0	_	-	mA	4
IOI _{GPIO-FAST_DSE_0}	I/O current sink capability measured when pad V_{ol} = 0.8 V	14.5	_	-	mA	4
loh _{GPIO-FAST_DSE_1}	I/O current sink capability measured when pad $V_{oh} = V_{DD} - 0.8 V$	21	_	-	mA	4
IOI _{GPIO-FAST_DSE_1}	I/O current sink capability measured when pad V_{ol} = 0.8 V	20.5	_	-	mA	4
IOHT	Output high current total for all ports	_	_	100	mA	
IIN	Input leakage current (per pin) for full te	mperature r	ange at V _{DE}	₀ = 5.5 V	L	5
	All pins other than high drive port pins		0.005	0.5	μA	
	High drive port pins		0.010	0.5	μA	1
R _{PU}	Internal pullup resistors	20		50	kΩ	6
R _{PD}	Internal pulldown resistors	20		50	kΩ	7

Table 12. DC electrical specifications at 5.0 V Range

1. For reset pads, same V_{ih} levels are applicable

2. For reset pads, same V_{il} levels are applicable

- 3. The strong pad I/O pin is capable of switching a 50 pF load up to 40 MHz.
- 4. For refernce only. Run simulations with the IBIS model and custom board for accurate results.

I/O parameters

Symbol	DSE	Rise ti	me (nS) ¹	Fall time (nS) ¹		Capacitance (pF) ²
		Min.	Max .	Min.	Max.	
		17.3	54.8	17.6	59.7	200
	1	1.1	4.6	1.1	5.0	25
		2.0	5.7	2.0	5.8	50
		5.4	16.0	5.0	16.0	200
tRF _{GPIO-FAST}	0	0.42	2.2	0.37	2.2	25
		2.0	5.0	1.9	5.2	50
		9.3	18.8	8.5	19.3	200
	1	0.37	0.9	0.35	0.9	25
		1.2	2.7	1.2	2.9	50
		6.0	11.8	6.0	12.3	200

Table 14. AC electrical specifications at 5 V Range (continued)

1. For reference only. Run simulations with the IBIS model and your custom board for accurate results.

2. Maximum capacitances supported on Standard IOs. However interface or protocol specific specifications might be different, for example for ENET, QSPI etc. . For protocol specific AC specifications, see respective sections.

5.7 Standard input pin capacitance

Table 15. Standard input pin capacitance

Symbol	Description	Min.	Max.	Unit
C _{IN_D}	Input capacitance: digital pins		7	pF

NOTE

Please refer to External System Oscillator electrical specifications for EXTAL/XTAL pins.

5.8 Device clock specifications

Table 16. Device clock specifications 1

Symbol	Description	Min.	Max.	Unit
	High Speed run mode ²			
f _{SYS}	System and core clock	_	112	MHz
f _{BUS}	Bus clock	—	56	MHz
f _{FLASH}	Flash clock	_	28	MHz
	Normal run mode (S32K11x series)		
f _{SYS}	System and core clock	—	48	MHz
f _{BUS}	Bus clock		48	MHz

Table continues on the next page...

6.2.4 Low Power Oscillator (LPO) electrical specifications Table 21. Low Power Oscillator (LPO) electrical specifications

Symbol	Parameter	Min.	Тур.	Max.	Unit
F _{LPO}	Internal low power oscillator frequency	113	128	139	kHz
T _{startup}	Startup Time	—		20	μs

6.2.5 SPLL electrical specifications

Table 22. SPLL electrical specifications

Symbol	Parameter	Min.	Тур.	Max.	Unit
F _{SPLL_REF} ¹	PLL Reference Frequency Range	8	—	16	MHz
F _{SPLL_Input} ²	PLL Input Frequency	8	—	40	MHz
F _{VCO_CLK}	VCO output frequency	180	—	320	MHz
F _{SPLL_CLK}	PLL output frequency	90	—	160	MHz
J _{CYC_SPLL}	PLL Period Jitter (RMS) ³				
	at F _{VCO_CLK} 180 MHz	_	120	_	ps
	at F _{VCO_CLK} 320 MHz	—	75	_	ps
J _{ACC_SPLL}	PLL accumulated jitter over 1µs (RMS) ³				
	at F _{VCO_CLK} 180 MHz	_	1350	_	ps
	at F _{VCO_CLK} 320 MHz	—	600	—	ps
D _{UNL}	Lock exit frequency tolerance	± 4.47	—	± 5.97	%
T _{SPLL_LOCK}	Lock detector detection time ⁴	_		150 × 10 ⁻⁶ + 1075(1/F _{SPLL_REF})	S

1. F_{SPLL_REF} is PLL reference frequency range after the PREDIV. For PREDIV and MULT settings refer SCG_SPLLCFG register of Reference Manual.

 F_{SPLL_Input} is PLL input frequency range before the PREDIV must be limited to the range 8 MHz to 40 MHz. This input source could be derived from a crystal oscillator or some other external square wave clock source using OSC bypass mode. For external clock source settings refer SCG_SOSCCFG register of Reference Manual.

3. This specification was obtained using a NXP developed PCB. PLL jitter is dependent on the noise characteristics of each PCB and results will vary

4. Lock detector detection time is defined as the time between PLL enablement and clock availability for system use.

6.3 Memory and memory interfaces

6.3.1 Flash memory module (FTFC) electrical specifications

This section describes the electrical characteristics of the flash memory module.

Symbol	Description ¹		S32	K116	S32K118			
			Тур	Max	Тур	Max	Unit	Notes
t _{eewr32b}	32-bit write to FlexRAM execution time	32 KB EEPROM backup	630	2000	630	2000	μs	3,4
		48 KB EEPROM backup	_	_	_	—		
		64 KB EEPROM backup	-	-	-	_		
t _{quickwr}	32-bit Quick Write execution time: Time from CCIF clearing (start the write) until CCIF setting (32-bit write complete, ready for next 32-bit write)	1st 32-bit write	200	550	200	550	μs	4,5,6
		2nd through Next to Last (Nth-1) 32-bit write	150	550	150	550		
		Last (Nth) 32-bit write (time for write only, not cleanup)	200	550	200	550		
t _{quickwrClnup}	Quick Write Cleanup execution time		_	(# of Quick Writes) * 2.0	_	(# of Quick Writes) * 2.0	ms	7

Table 24. Flash command timing specifications for S32K11x (continued)

- 1. All command times assume 25 MHz or greater flash clock frequency (for synchronization time between internal/external clocks).
- 2. Maximum times for erase parameters based on expectations at cycling end-of-life.
- For all EEPROM Emulation terms, the specified timing shown assumes previous record cleanup has occurred. This may be verified by executing FCCOB Command 0x77, and checking FCCOB number 5 contents show 0x00 - No EEPROM issues detected.
- 4. 1st time EERAM writes after a Reset or SETRAM may incur additional overhead for EEE cleanup, resulting in up to 2x the times shown.
- 5. Only after the Nth write completes will any data be valid. Emulated EEPROM record scheme cleanup overhead may occur after this point even after a brownout or reset. If power on reset occurs before the Nth write completes, the last valid record set will still be valid and the new records will be discarded.
- 6. Quick Write times may take up to 550 µs, as additional cleanup may occur when crossing sector boundaries.
- 7. Time for emulated EEPROM record scheme overhead cleanup. Automatically done after last (Nth) write completes, assuming still powered. Or via SETRAM cleanup execution command is requested at a later point.

NOTE

Under certain circumstances FlexMEM maximum times may be exceeded. In this case the user or application may wait, or assert reset to the FTFC macro to stop the operation.

6.3.1.2 Reliability specifications

Table 25. NVM reliability specifications

Symbol	Description	Min.	Тур.	Max.	Unit	Notes		
When using as Program and Data Flash								
t _{nvmretp1k}	Data retention after up to 1 K cycles	20	—	—	years	1		
n _{nvmcycp}	Cycling endurance	1 K		_	cycles	2, 3		

Table continues on the next page ...



Figure 9. QuadSPI input timing (SDR mode) diagram



Figure 10. QuadSPI output timing (SDR mode) diagram



TIS-Setup Time TIH-Hold Time

Figure 11. QuadSPI input timing (HyperRAM mode) diagram

Symbol	Description	Conditions	Min.	Typ. ¹	Max.	Unit	Notes
f _{ADCK}	ADC conversion clock frequency	Normal usage	2	40	50	MHz	3, 4
f _{CONV}	ADC conversion frequency	No ADC hardware averaging. ⁵ Continuous conversions enabled, subsequent conversion time	46.4	928	1160	Ksps	6, 7
		ADC hardware averaging set to 32. ⁵ Continuous conversions enabled, subsequent conversion time	1.45	29	36.25	Ksps	6, 7

Table 27. 12-bit ADC operating conditions (continued)

- 1. Typical values assume $V_{DDA} = 5 V$, Temp = 25 °C, $f_{ADCK} = 40 \text{ MHz}$, $R_{AS}=20 \Omega$, and $C_{AS}=10 \text{ nF}$ unless otherwise stated. Typical values are for reference only, and are not tested in production.
- For packages without dedicated V_{REFH} and V_{REFL} pins, V_{REFH} is internally tied to V_{DDA}, and V_{REFL} is internally tied to V_{SS}. To get maximum performance, reference supply quality should be better than SAR ADC. See application note AN5032 for details.
- 3. Clock and compare cycle need to be set according to the guidelines mentioned in the Reference Manual .
- 4. ADC conversion will become less reliable above maximum frequency.
- 5. When using ADC hardware averaging, see the *Reference Manual* to determine the most appropriate setting for AVGS.
- 6. Numbers based on the minimum sampling time of 275 ns.
- 7. For guidelines and examples of conversion rate calculation, see the Reference Manual section 'Calibration function'



Figure 13. ADC input impedance equivalency diagram

6.5 Communication modules

6.5.1 LPUART electrical specifications

Refer to General AC specifications for LPUART specifications.

6.5.1.1 Supported baud rate

Baud rate = Baud clock / ((OSR+1) * SBR).

For details, see section: 'Baud rate generation' of the Reference Manual.

6.5.2 LPSPI electrical specifications

The Low Power Serial Peripheral Interface (LPSPI) provides a synchronous serial bus with master and slave operations. Many of the transfer attributes are programmable. The following tables provide timing characteristics for classic LPSPI timing modes.

- All timing is shown with respect to 20% V_{DD} and 80% V_{DD} thresholds.
- All measurements are with maximum output load of 50 pF, input transition of 1 ns and pad configured with fastest slew setting (DSE = 1).

Communication modules

Table 32. LPSPI electrical specifications1 (continued)

N	Num Symbol Descript		Description	Conditions		Run	Mode ²			HSRU	N Mode ²			VLPR	Mode		Unit		
					5.0	V IO	3.3	V IO	5.0	V IO	3.3	V IO	5.0	V IO	3.3	/ 10			
					Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.			
	4	t _{Lag} 9	Enable lag	Slave	-	-	-	-	-	-	-	-	-	-	-	-	ns		
			time (After	Master		-		-		-		-		-		-			
				Master Loopback ⁵	- 25		- 25		- 25		- 25		- 50		- 50				
		Master Loopback(slow) ⁶	(SCKPCS+1)*t _{periph}		(SCKPCS+1)*t _{periph}		(SCKPCS+1)*t _{periph}		(SCKPCS+1)*t _{periph}		(SCKPCS+1)*t _{periph}		(SCKPCS+1)*t _{periph}						
	5	t _{WSPSCK} 10	Clock(SPSCK	Slave													ns		
) high or low time (SPSCK duty cycle)) high or low time (SPSCK duty cycle) Loopback) high or low time (SPSCK	Master	ဂု	ς +3	ကို	с +3	ကို	ς +3	ကို	ς + γ	2-5	1-2	- 2	+2	
		duty			Master Loopback ⁵	SPSCK/	sPSCK/2	SPSCK	sPSCK/2	SPSCK	sPSCK/2	SPSCK/2	sPSCK/2	SPSCK/2	sPSCK/2	SPSCK	spsck/2		
				Master Loopback(slow) ⁶	t t	÷,	1	<u>ب</u>	1	<u>ب</u>	t	ů,	4	ů,	t t	ţ			
	6	t _{SU}	Data setup	Slave	3	-	5	-	3	-	5	-	18	-	18	-	ns		
			time(inputs)	Master	29	-	38	-	26	-	37 ¹¹ 32 ¹²	-	72	-	78	-			
				Master Loopback ⁵	7	-	8	-	5	-	7	-	20	-	20	-			
				Master Loopback(slow) ⁶	8	-	10	-	7	-	9	-	20	-	20	-			
	7 t _{HI} Data hold	Data hold	Slave	3	-	3	-	3	-	3	-	14	-	14	-	ns			
			time(inputs)	Master	0	-	0	-	0	-	0	-	0	-	0	-			
			Master Loopback ⁵	3	-	3	-	2	-	3	-	11	-	11	-				
				Master Loopback(slow) ⁶	3	-	3	-	3	-	3	-	12	-	12	-			

Table continues on the next page...

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Table 32. LPSPI electrical specifications1 (continued)

Num	Symbol	Description	Conditions	Run Mode ²			HSRUN Mode ²			VLPR Mode				Unit		
				5.0 V IO		3.3 V IO		5.0 V IO 3.3 V		V IO 5.0 V IO		3.3 V IO				
				Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
			Master Loopback(slow) 6	-		-		-		-		-		-		

- 1. Trace length should not exceed 11 inches for SCK pad when used in Master loopback mode.
- 2. While transitioning from HSRUN mode to RUN mode, LPSPI output clock should not be more than 14 MHz.
- 3. f_{periph} = LPSPI peripheral clock
- 4. $t_{periph} = 1/f_{periph}$
- 5. Master Loopback mode In this mode LPSPI_SCK clock is delayed for sampling the input data which is enabled by setting LPSPI_CFGR1[SAMPLE] bit as 1. Clock pads used are PTD15 and PTE0. Applicable only for LPSPI0.
- 6. Master Loopback (slow) In this mode LPSPI_SCK clock is delayed for sampling the input data which is enabled by setting LPSPI_CFGR1[SAMPLE] bit as 1. Clock pad used is PTB2. Applicable only for LPSPI0.
- 7. This is the maximum operating frequency (f_{op}) for LPSPI0 with medium PAD type only. Otherwise, the maximum operating frequency (f_{op}) is 12 Mhz.
- 8. Set the PCSSCK configuration bit as 0, for a minimum of 1 delay cycle of LPSPI baud rate clock, where PCSSCK ranges from 0 to 255.
- 9. Set the SCKPCS configuration bit as 0, for a minimum of 1 delay cycle of LPSPI baud rate clock, where SCKPCS ranges from 0 to 255.
- 10. While selecting odd dividers, ensure Duty Cycle is meeting this parameter.
- 11. Maximum operating frequency (fop) is 12 MHz irrespective of PAD type and LPSPI instance.
- 12. Applicable for LPSPI0 only with medium PAD type, with maximum operating frequency (f_{op}) as 14 MHz.

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Figure 21. LPSPI slave mode timing (CPHA = 1)

6.5.3 LPI2C electrical specifications

See General AC specifications for LPI2C specifications.

For supported baud rate see section 'Chip-specific LPI2C information' of the *Reference Manual*.

Communication modules



Figure 23. SAI Timing — Slave modes

6.5.6 Ethernet AC specifications

The following timing specs are defined at the chip I/O pin and must be translated appropriately to arrive at timing specs/constraints for the physical interface.

The following table describes the MII electrical characteristics.

- Measurements are with maximum output load of 25 pF, input transition of 1 ns and pad configured with fastest slew settings (DSE = 1'b1).
- I/O operating voltage ranges from 2.97 V to 3.6 V
- While doing the mode transition (RUN -> HSRUN or HSRUN -> RUN), the interface should be OFF.

Symbol	Description	Min.	Max.	Unit
_	RXCLK frequency	—	25	MHz
MII1	RXCLK pulse width high	35%	65%	RXCLK period
MII2	RXCLK pulse width low	35%	65%	RXCLK period
MII3	MII3 RXD[3:0], RXDV, RXER to RXCLK setup		_	ns
MII4	RXCLK to RXD[3:0], RXDV, RXER hold	5	_	ns
—	TXCLK frequency	_	25	MHz
MII5	TXCLK pulse width high	35%	65%	TXCLK period
MII6	TXCLK pulse width low	35%	65%	TXCLK period
MII7	MII7 TXCLK to TXD[3:0], TXEN, TXER invalid			ns
MII8 TXCLK to TXD[3:0], TXEN, TXER valid		_	25	ns

Table 35. MII signal switching specifications

Communication modules



Figure 24. MII receive diagram



Figure 25. MII transmit signal diagram

The following table describes the RMII electrical characteristics.

- Measurements are with maximum output load of 25 pF, input transition of 1 ns and pad configured with fastest slew settings (DSE = 1'b1).
- I/O operating voltage ranges from 2.97 V to 3.6 V
- While doing the mode transition (RUN -> HSRUN or HSRUN -> RUN), the interface should be OFF.

Symbol	Description	Min.	Max.	Unit
—	RMII input clock RMII_CLK Frequency	—	50	MHz
RMII1, RMII5	RMII_CLK pulse width high	35%	65%	RMII_CLK period
RMII2, RMII6	RMII_CLK pulse width low	35%	65%	RMII_CLK period
RMII3	RXD[1:0], CRS_DV, RXER to RMII_CLK setup	4	—	ns
RMII4	RMII_CLK to RXD[1:0], CRS_DV, RXER hold	2		ns

Table continues on the next page...

Table 42. Thermal characteristics for the 100 MAPBGA package

Rating	Conditions	Symbol		Values		
			S32K146	S32K144	S32K148	
Thermal resistance, Junction to Ambient (Natural Convection) ^{1, 2}	Single layer board (1s)	$R_{ extsf{ heta}JA}$	57.2	61.0	52.5	°C/W
Thermal resistance, Junction to Ambient (Natural Convection) ^{1, 2, 3}	Four layer board (2s2p)	R _{θJA}	32.1	35.6	27.5	°C/W
Thermal resistance, Junction to Ambient (@200 ft/min) 1, 2, 3	Single layer board (1s)	R _{0JMA}	44.1	46.6	39.0	°C/W
Thermal resistance, Junction to Ambient (@200 ft/min) ^{1, 3}	Two layer board (2s2p)	R _{θJMA}	27.2	30.9	22.8	°C/W
Thermal resistance, Junction to Board ⁴	—	R _{θJB}	15.3	18.9	11.2	°C/W
Thermal resistance, Junction to Case ⁵	—	R _{θJC}	10.2	14.2	7.5	°C/W
Thermal resistance, Junction to Package Top outside center ⁶	—	Ψյτ	0.2	0.4	0.2	°C/W
Thermal resistance, Junction to Package Bottom outside center ⁷	—	Ψјв	12.2	15.9	18.3	°C/W

1. Junction temperature is a function of die size, on-chip power dissipation, package thermal resistance, mounting site (board) temperature, ambient temperature, air flow, power dissipation of other components on the board, and board thermal resistance.

2. Per SEMI G38-87 and JEDEC JESD51-2 with the single layer board horizontal.

3. Per JEDEC JESD51-6 with the board horizontal.

4. Thermal resistance between the die and the printed circuit board per JEDEC JESD51-8. Board temperature is measured on the top surface of the board near the package.

5. Thermal resistance between the die and the case top surface as measured by the cold plate method (MIL SPEC-883 Method 1012.1).

6. Thermal characterization parameter indicating the temperature difference between package top and the junction temperature per JEDEC JESD51-2. When Greek letters are not available, the thermal characterization parameter is written as Psi-JT.

7. Thermal characterization parameter indicating the temperature difference between package bottom center and the junction temperature per JEDEC JESD51-12. When Greek letters are not available, the thermal characterization parameter is written as Psi-JB.

S32K1xx Data

۱ Sheet,

Rev.

<u>,</u>

06/2018

Table 43.	Revision	History
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Rev. No.	Date	Substantial Changes
		 Added footnote 'For S32K11x – FIRC/SOSC/FIRC/LPO; For S32K14x
		- FIRC/SOSC/FIRC/LPO/SPLL' to 'VLPS Mode: All clock sources
		disabled'
		Updated numbers for: A VLPP - VLPP
		 VLFN → VLFS V/LPS → V/LPB
		'BLIN → Compute operation'
		 RUN → VLPS
		RUN → VLPR
		In Power consumption :
		 Updated specs for S32K142, S32K144, and S32K148
		 Updated footnote 'Typical current numbers are indicative'
		 Updated footnote 'The S32K148 data'
		Removed footnote 'Above S32K148 data is preliminary targets only'
		Added new table 'Power consumption at 3.3 V'
		Indeneral AC specifications : Indeted may value and footnote of WERST
		Undated symbol for not filtered pulse to 'WNERST' undated min value
		removed max, value, and added footnote
		Fixed naming conventions to align with DS in DC electrical specifications at
		3.3 V Range and DC electrical specifications at 5.0 V Range
		 Updated specs for AC electrical specifications at 3.3 V range and AC
		electrical specifications at 5 V range
		In Device clock specifications :
		Updated f _{BUS} to 48 for 11x
		Added foothote to f _{BUS} for 14x
		In External System Oscillator frequency specifications : Added space for S32K11y
		Updated 'the exter' for \$32K14x
		 Added footnote 'Frequecies below ' to 'fec extal ' and 'tdc extal '
		 Splitted Flash timing specifications — commands for S32K14x and S32K11x
		 Updated Flash timing specifications — commands for S32K14x
		In Reliability specifications :
		 Added footnote 'Data retention period ' for 'tnvmretp1k' and
		'Invmretee'
		In OuadSPLAC specifications:
		Updated 'MCB[SCI KCEG[5]]' value to 0
		Updated 'Data Input Setup Time' HSRUN Internal DQS PAD Loopback
		value to 1.6
		 Updated 'Data Input Setup Time' DDR External DQS min. value to 2
		 Updated 'Data Input Hold Time' DDR External DQS min. value to 20
		Upadted figure 'QuadSPI output timing (SDR mode) diagram' and
		'QuadSPI input timing (HyperHAM mode) diagram'
		III 12-bit ADC electrical characteristics : Added note 'On reduced nin packages where '
		Removed max, value of 'look app'
		Added note 'Due to triple '
		• In 12-bit ADC operating conditions, removed parameter ' ΔV_{DDA} '
		In CMP with 8-bit DAC electrical specifications :
		 Updated Typ. and Max. values of 'I_{DDLS}'
		Upadted Typ. value of 't _{DHSB} '
		 Updated Typ. value of 'V_{HYST1}', 'V_{HYST2}', and 'V_{HYST3}'
		In LPSPI electrical specifications :
		• Updated Tperiph and Top', and TSPSCK

Table continues on the next page...

Rev. No.

Date

		 Updated 3.3 V numbers and added footnote against f_{op}, t_{SU}, ans t_V in HSRUN Mode Added footnote to 't_{WSPSCK}' Updated Thermal characteristics for S32K11x
6	31 Jan 2018	 Changed the representation of ARM trademark throughout. Removed S32K142 from 'Caution' In 'Key features', added the following note under 'Power management', 'Memory and memory interfaces', and 'Reliability, safety and security': No write or erase access to In High-level architecture diagram for the S32K14x family, added the following footnote: No write or erase access to In High-level architecture diagram for the S32K11x family : No write or erase access to In High-level architecture diagram for the S32K11x family : No write or erase access to In High-level architecture diagram for the S32K11x family : Minor editorial update: Fixed the placement of SRAM, under 'Flash memory controller' block Updated figure: S32K1xx product series comparison : Updated footnote 1, and added against 'HSRUN' in addition to 'HW security module (CSEc)' and 'EEPROM emulated by FlexRAM'. Updated 'System RAM (including FlexRAM and MTB)' row for S32K144, S32K146, and S32K148. Updated channel count for S32K116 in row '12-bit SAR ADC (1 MSPS each)'. Updated Ordering information Updated Flash timing specifications — commands for S32K148, S32K142, S32K146, S32K116, and S32K118.
7	19 April 2018	 Changed Caution to Notes Updated the wordings of Notes and removed S32K146 Added 'Following two are the available' In 'Key features': Editorial updates Updated the note under Power management, Memory and memory interfaces, and Safety and security. Updated FlexIO under Communications interfaces Added ENET and SAI under Communications interfaces Updated Cryptographic Services Engine (CSEc) under 'Safety and security' In High-level architecture diagram for the S32K14x family : Minor editorial updates Updated note 3 In High-level architecture diagram for the S32K11x family : Minor editorial updates Updated note 3 In High-level architecture diagram for the S32K11x family : Minor editorial updates Updated note 3 In High-level architecture diagram for the S32K11x family : Minor editorial updates Updated note 3 In Figure: S32K1xx product series comparison : Editorial updates Updated Frequency for S32K14x Updated footnote 4 Added footnote 5 In Ordering information : Renamed section, updated the starting paragraph Updated the figure In Voltage and current operating requirements, updated the note In Power consumption : Updated specs for S32K146 Removed section 'Modes configuration', and moved its content under

Table 43. Revision History (continued)

Substantial Changes

Table continues on the next page...

the fisrt paragraph.

In 12-bit ADC operating conditions :



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